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APPLICANTS

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\*\* CONTINUING DATA \*\*\*\*\* *none* *K-CC*

\*\* FOREIGN APPLICATIONS \*\*\*\*\* *K-CC*  
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IF REQUIRED, FOREIGN FILING LICENSE GRANTED  
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Foreign Priority claimed 35 USC 119 (a-d) conditions met Verified and Acknowledged	<input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after Allowance <i>K-CC</i> Examiner's Signature Initials	STATE OR COUNTRY KOREA, REPUBLIC OF	SHEETS DRAWING 4	TOTAL CLAIMS 19	INDEPENDENT CLAIMS 2
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TITLE  
 Method for manufacturing multi-thickness gate dielectric layer of semiconductor device

☐ All Fees